NSN 5961-01-274-5233

Transistor - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5961-01-274-5233

Inclosure Material:

Metal

Overall Length:

Between 0.160 inches and 0.180 inches

Terminal Length:

Between 0.500 inches and 0.750 inches

Overall Diameter:

Between 0.335 inches and 0.370 inches

Internal Configuration:

Field effect

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-205af

Electrode Internally-electrically Connected To Case:

Drain

Mounting Method:

Terminal **Terminal Circle Diameter:**

0.200 inches

Features Provided:

Quality assurance level txv

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

100.0 drain to source voltage and 100.0 drain to gate voltage and 20.0 gate to source voltage

Current Rating Per Characteristic:

6.00 amperes drain current and 6.00 amperes source current and 24.00 amperes off-state current, peak

Power Rating Per Characteristic:

20.0 watts total power dissipation

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

3 uninsulated wire lead

Specification Data:

81349-mil-s-19500/555 government specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

NSN 5961-01-274-5233 Transistor - Page 2 of 2

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